

5. (Original) The method of manufacturing a semiconductor device according to claim 3, wherein the PE-USG oxide layer is formed by using  $\text{SiH}_4$  as a source gas and by combining  $\text{N}_2\text{O}$  or  $\text{O}_2$  therewith.

6. (Amended) The method of manufacturing a semiconductor device according to claim 5, wherein the PE-USG oxide layer is deposited under the conditions that the flow rate of  $\text{SiH}_4$  is between 10 and 200 sccm, that the flowrate of  $\text{N}_2\text{O}$  and  $\text{O}_2$  is between 100 and 3000 sccm, the flowrate of He is between 0 and ~~1000 sccm~~ 1000 sccm, the pressure is between 0.1 and 50 Torr, the temperature is between 350 and 550°, and the power is between 100 and 1000W.

7. (Original) The method of manufacturing a semiconductor device according to claim 3, wherein the PE-USG oxide layer has a thickness of between 300 and 1000Å and step coverage is below 50%.

8. (Amended) The method of manufacturing a semiconductor device according to claim 1, wherein the ~~selectively of the selective~~ conductive plug is formed by growing a selective single crystal silicon and a selective polycrystalline silicon by using a LPCVD method or a UHVCVD method.

9. (Amended) The method of manufacturing a semiconductor device according to claim 8, wherein a Si-H-Cl system is first used with the LPCVD method and a dichlorosilane ~~DCS~~- $\text{H}_2$ -HCl or Methylsilane ~~MS~~- $\text{H}_2$ -HCl gas system is then used.